

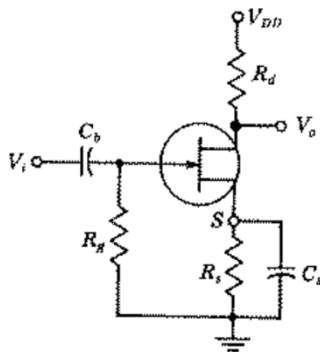
## Assignment 2

### Analog Electronics (EC-261)

Max. Marks: 10

**Note: All questions are compulsory.**

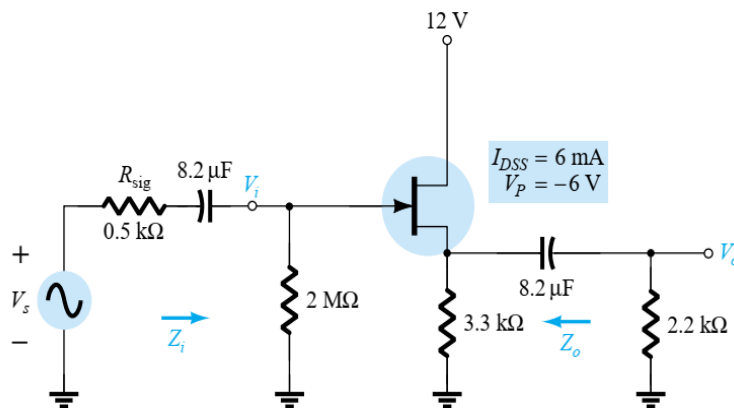
Q.1 The amplifier of Fig. 1 utilizes an n-channel JFET for which  $V_p = -2.0$  V,  $I_{DSS} = 1.65$  mA. It is desired to bias the circuit at  $I_D = 0.8$  mA, using  $V_{DD} = 24$  V. Assume  $r_d \gg R_D$ . Find (a)  $V_{GS}$  (b)  $g_m$  (c)  $R_s$  and (d)  $R_d$ , such that voltage gain at least 20 db, with  $R_s$  bypassed with a very large capacitance  $C_s$ .



**Fig. 1**

Q.2 For the network of Fig. 2:

- Determine  $A_{vNL}$ ,  $Z_i$ , and  $Z_o$ .
- Determine  $A_v$  and  $A_{vs}$ .
- Change  $R_L$  to  $4.7$  k $\Omega$  and calculate  $A_v$  and  $A_{vs}$ . What was the effect of increasing levels of  $R_L$  on both voltage gains?
- Change  $R_{sig}$  to  $1$  k $\Omega$  (with  $R_L$  at  $2.2$  k $\Omega$ ) and calculate  $A_v$  and  $A_{vs}$ . What was the effect of increasing levels of  $R_{sig}$  on both voltage gains?
- Change  $R_L$  to  $4.7$  k $\Omega$  and  $R_{sig}$  to  $1$  k $\Omega$  and calculate  $Z_i$  and  $Z_o$ . What was the effect on both parameters?



**Fig. 2**

Q.3 The self-bias configuration has an operating point defined by  $V_{GSQ} = -2.6$  V and  $I_{DQ} = 2.6$  mA, with  $I_{DSS} = 8$  mA and  $V_P = -6$  V. The network is redrawn as Fig. 3 with an applied signal  $V_i$ . The value of  $y_{os}$  is given as 20 S.

- Determine  $g_m$ ,  $r_d$ ,  $Z_i$ .
- Calculate  $Z_o$  with and without the effects of  $r_d$ . Compare the results.
- Calculate  $A_v$  with and without the effects of  $r_d$ . Compare the results.

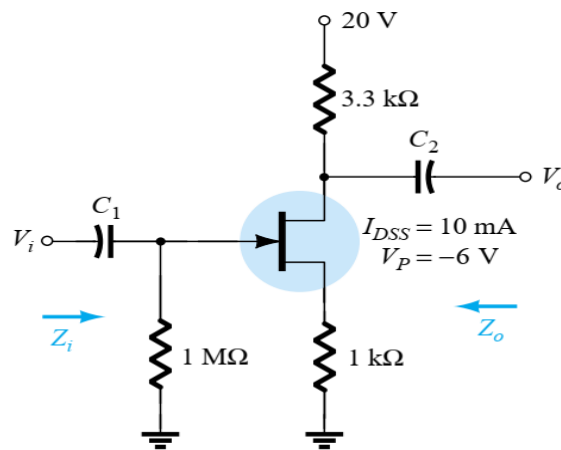


Fig. 3

Q.4 Determine the following for the network of Fig. 4.

- $I_{DQ}$  and  $V_{GSQ}$
- $V_{DS}$
- $V_D$
- $V_S$

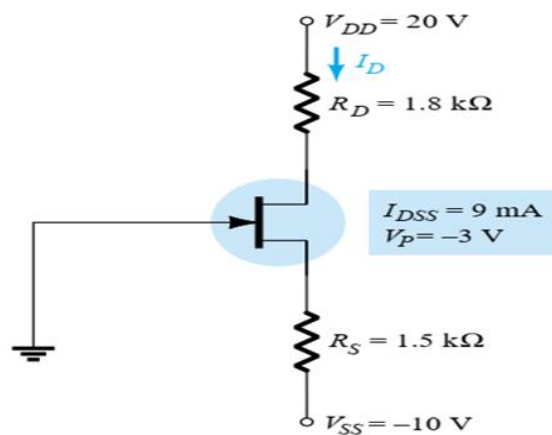


Fig. 4